



PRODUCT DATA SHEET



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Datasheet

Samples

Please note: Please check the JINGAO Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.jg-semi.cn. Please email any questions regarding the system integration to JINGAO_questions@jgsemi.com.

PNP Silicon Epitaxial Planar Transistor

Features

- High saturation voltage
- Excellent hFE linearity

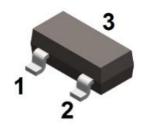
Mechanical Data

Case: SOT-23

Molding Compound: UL Flammability Classification Rating 94V-0

Terminals: Matte tin-plated leads; solderability-per MIL-STD-202,

Method 208



SOT-23

Maximum Ratings (@ TA = 25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Collector-Base Breakdown Voltage	V _{CBO}	-500	V
Collector-Emitter Breakdown Voltage	VCEO	-500	V
Emitter-Base Breakdown Voltage	V _{EBO}	-7	V
Collector Current (Continuous)	Ic	-0.15	Α
Collector Current (Peak)	Ісм	-0.5	Α

Thermal Characteristics

Parameter	Symbol	Value	Unit
Power Dissipation(T _A = 25°C)	PD	500	mW
Thermal Resistance Junction-to-Air *1	$R_{\theta JA}$	212	°C/W
Thermal Resistance Junction-to-Case *1	R _θ JC	110	°C/W
Junction Temperature Range	TJ	-55 ~ +150	°C
Storage Temperature Range	T _{STG}	-55 ~ +150	°C

Note 1: The data tested by surface mounted on a minimum recommended FR-4 board

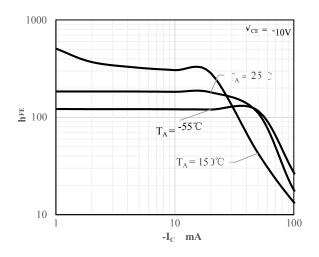


Electrical Characteristics (@ T_A = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Collector-Base Breakdown Voltage	V _{(BR)CBO}	$I_C = -100\mu A, I_E = 0$	-500	-	-	V
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	$I_C = -1 \text{mA}, I_B = 0$	-500	-	-	٧
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	I _E = -100μA, I _C = 0	-7	-	-	٧
Collector Cut-off Current	Ісво	V _{CB} = -500V, I _E = 0	-	-	-0.1	μΑ
Collector Cut-off Current	I _{CEX}	V _{CE} = -500V, R _{BE} =1k	-	-	-0.1	μA
Emitter Cut-off Current	I _{EBO}	V _{EB} = -5V, I _C = 0	-	-	-0.1	μΑ
DC Current Gain	hfE	V _{CE} = -10V, I _C = -1mA	100	-	300	-
		V _{CE} = -10V, I _C = -50mA	80	-	300	-
		V _{CE} = -10V, I _C = -100mA	-	15	-	-
Collector-emitter Saturation Voltage V _{CE(sat)}		I _C = -20mA, I _B = -2mA	-	-	-0.2	٧
	I _C = -50mA, I _B = -10mA	-	-	-0.5	٧	
Base-emitter Saturation Voltage	V _{BE(sat)}	I _C = -50mA, I _B = -10mA	-	-	-0.9	٧
Base-emitter Voltage	V _{BE(on)}	V _{CE} = -10V, I _C = -50mA	-	-	-0.9	٧
Transition Frequency	f⊤	I _C = -10mA, V _{CE} = -20V	60	-	-	MHz
		f = 50MHz				·
Output Capacitance	C _{ob}	$V_{CB} = -20V$, $I_E = 0A$, $f = 1MHz$	-	-	8	pF



Ratings and Characteristics Curves (@ TA = 25°C unless otherwise specified)



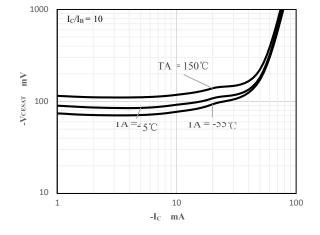
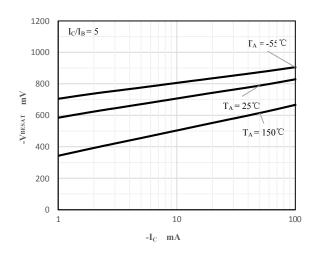


Fig 1 hFE vs. Ic

Fig 2 V_{CE(sat)} vs. I_C

100



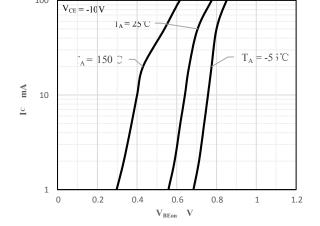
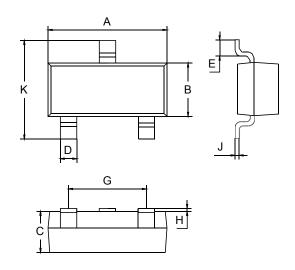


Fig 3 V_{BE(sat)} vs. Ic

Fig 4 V_{BE(ON)} vs. Ic



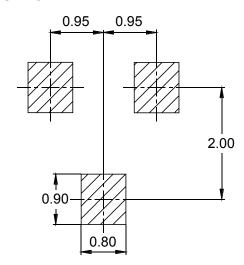
Package Outline Dimensions (Unit: mm)



SOT-23			
	Min.	Max.	
Α	2.70	3.10	
В	1.10	1.50	
С	0.90	1.10	
D	0.30	0.50	
E	0.35	0.48	
G	1.80	2.00	
Н	0.02	0.10	
J	0.05	0.15	
K	2.20	2.60	

Package Outline Dimensions (Unit: mm)

SOT-23





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